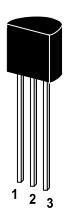
NPN Silicon Epitaxial Planar Transistor

for switching and general purpose applications.

The transistor is subdivided into two groups, O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25°C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	35	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	Ic	500	mA
Emitter Current	I _E	-500	mA
Power Dissipation	P _{tot}	625	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







ST 2SC3202

Characteristics at T_{amb}=25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V _{CE} =1V, I _C =100mA						
Current Gain Group)					
	0	h_{FE}	70	-	140	-
	Υ	h_{FE}	120	-	240	-
at V _{CE} =6V, I _C =400mA	0	h_{FE}	25	-		
	Υ	h_{FE}	40	-	-	
Collector Cutoff Current						
at V _{CB} =35V		I_{CBO}	-	-	0.1	μΑ
Emitter Cutoff Current						
at V _{EB} =5V		I_{EBO}	-	-	0.1	μΑ
Collector Emitter Saturation Voltage						
at I _C =100mA, I _B =10mA		$V_{\text{CE(sat)}}$	-	0.1	0.25	V
Base Emitter Voltage						
at V _{CE} =1V, I _C =100mA		V_{BE}	-	0.8	1	V
Transition Frequency						
at V _{CE} =6V, I _C =20mA		f_T	-	300	-	MHz
Collector Output Capacitance						
at V _{CB} =6V, f=1MHz		C_OB	-	7.0	-	pF









SEMTECH ELECTRONICS LTD.